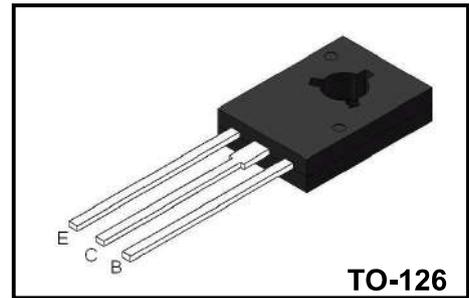


Plastic-Encapsulate Transistors(PNP)



**FEATURES**

- ◆ Low saturation voltage
- ◆ High Power Dissipation :  $P_C=1.5W(T_a=25^{\circ}C)$
- ◆ Complement to KTD1691

**Absolute Maximum Ratings (Ta=25°C)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$BV_{CBO}$	-60	V
Collector-Emitter Voltage	$BV_{CEO}$	-60	V
Emitter-Base Voltage	$BV_{EBO}$	-7	V
Collector Current	$I_C$	-5	A
Collector Power Dissipation	$P_C$	1.5	W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~150	°C

**Electrical Characteristics (Ta=25°C)**

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Collector-base breakdown voltage	$I_C = -100\mu A, I_E = 0$	$BV_{CBO}$	-60			V
Collector-emitter breakdown voltage	$I_C = -10mA, I_B = 0$	$BV_{CEO}$	-60			V
Emitter-base breakdown voltage	$I_E = -100\mu A, I_C = 0$	$BV_{EBO}$	-7			V
Collector cut-off current	$V_{CB} = -50V, I_E = 0$	$I_{CBO}$			-10	$\mu A$
Emitter cut-off current	$V_{EB} = -7V, I_C = 0$	$I_{EBO}$			-10	$\mu A$
DC current gain*	$V_{CE} = -1V, I_C = -0.1A$	$h_{FE1}$	60			
	$V_{CE} = -1V, I_C = -2A$	$h_{FE2}$	160		400	
	$V_{CE} = -2V, I_C = -5A$	$h_{FE3}$	50			
Collector-emitter saturation voltage*	$I_C = -2A, I_B = -0.2A$	$V_{CE(sat)}$			-0.3	V
Base-emitter saturation voltage*	$I_C = -2A, I_B = -0.2A$	$V_{BE(sar)}$			-1.2	V

\* Pulse test: Pulse Width  $\leq 300\mu s$  ; Duty cycle  $\leq 2\%$ .

**$h_{FE} 2$  Classification**

Classification	2SB1151-O	2SB1151-Y
Range	160-320	200-400

Typical Characteristics

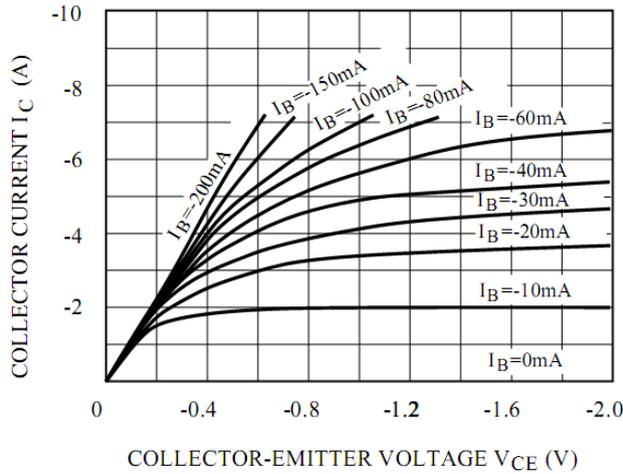


Figure 1. Static Characteristic

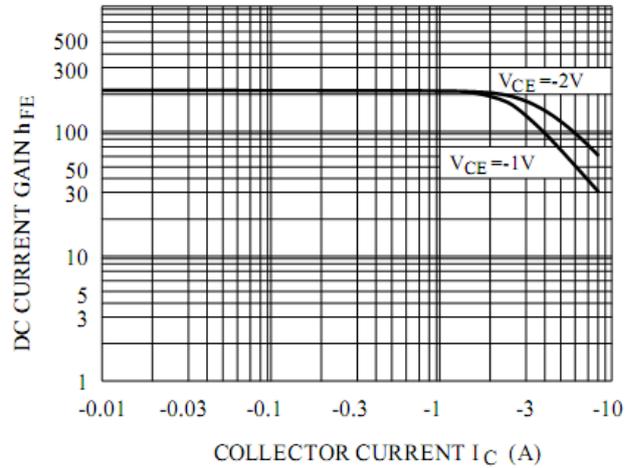


Figure 2. DC current Gain

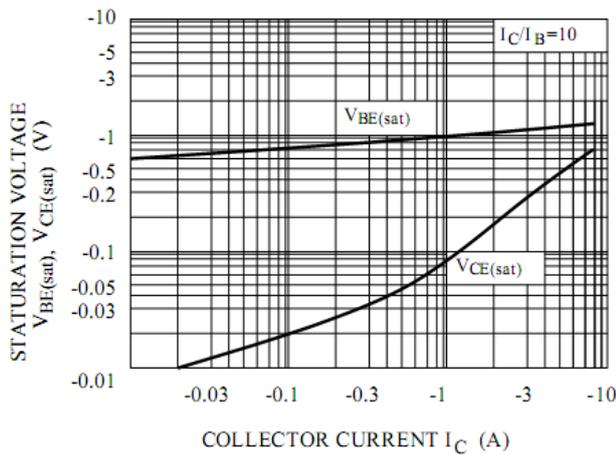


Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

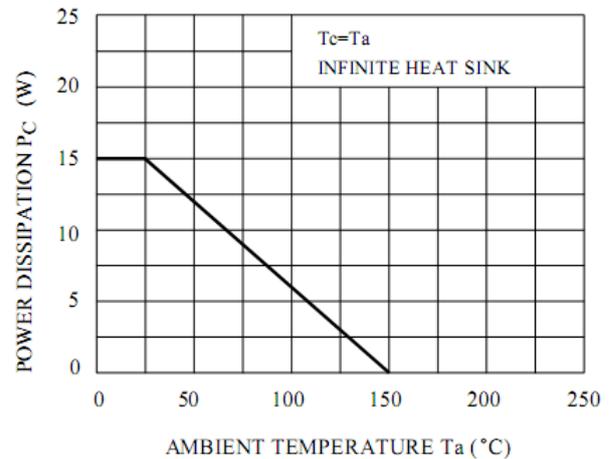


Figure 4. Power Derating

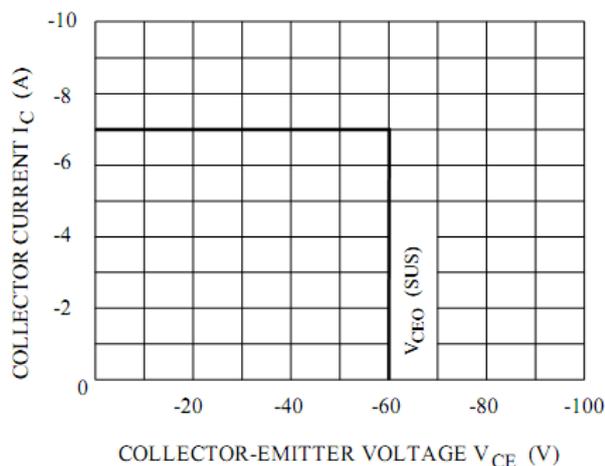


Figure 5. Reverse Bias Safe Operating Area

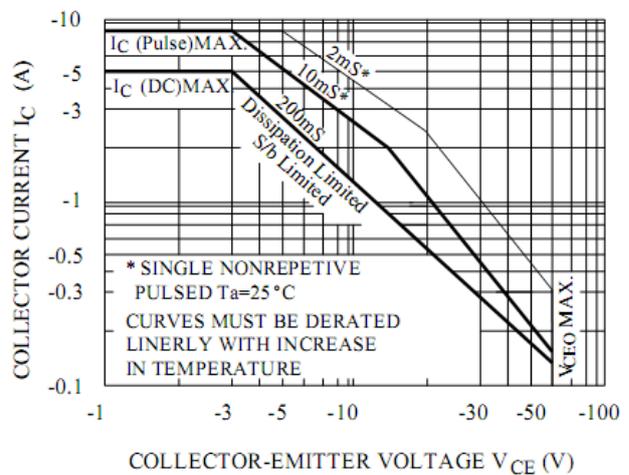


Figure 6. Safe Operating Area

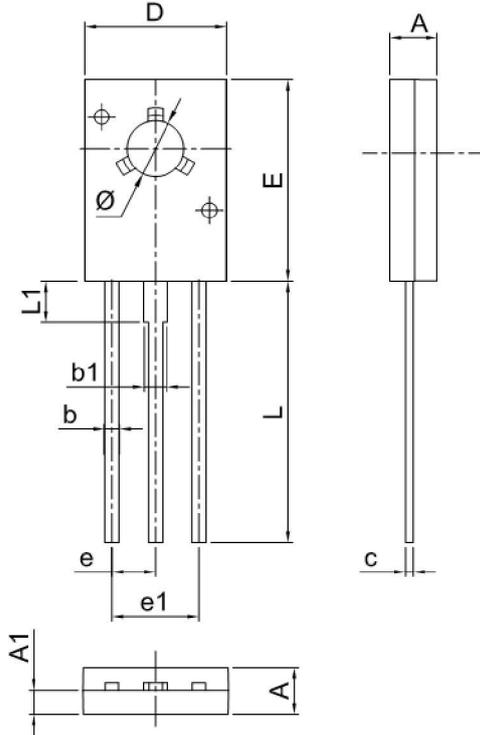
**Ordering information**

Package	Packing Description	Base Quantity
TO-126	Bulk	500pcs/Bag

**Package Dimensions**

**TO-126**

Symbol	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.40	2.80	0.094	0.110
A1	1.00	1.40	0.039	0.055
b	0.66	0.86	0.026	0.034
b1	1.17	1.37	0.046	0.054
c	0.40	0.60	0.016	0.024
D	7.30	7.70	0.287	0.303
E	10.60	11.00	0.417	0.433
e	2.25	2.33	0.089	0.092
e1	4.50	4.66	0.177	0.183
L	14.00	15.00	0.551	0.591
L1	1.90	2.50	0.075	0.098
Φ	3.10	3.30	0.122	0.130



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